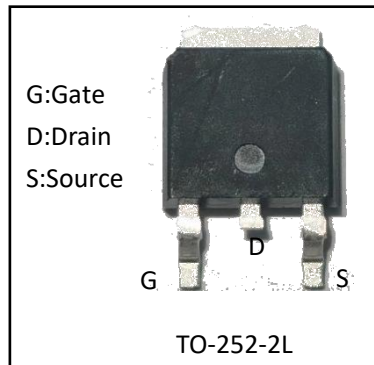


GENERAL DESCRIPTION

The product is an N-channel mode power MOSFET using advanced technology to provide customers with planar stripe. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

FEATURE

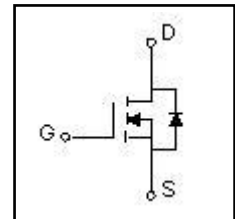
- Excellent package for good heat dissipation
- High switching speed
- 100% avalanche tested



APPLICATION

- Power switching application
- Power switching application

EQUIVALENT CIRCUIT



MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current	2.0	A
I_{DM}	Pulsed Drain Current	16	A
P_D	Power Dissipation	48	W
T_j	Junction Temperature	-45 to 125	°C
T_{stg}	Storage Temperature		
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	62.5	°C/W
$R_{\theta JC}$	Thermal Resistance From Junction To Case	2.6	°C/W

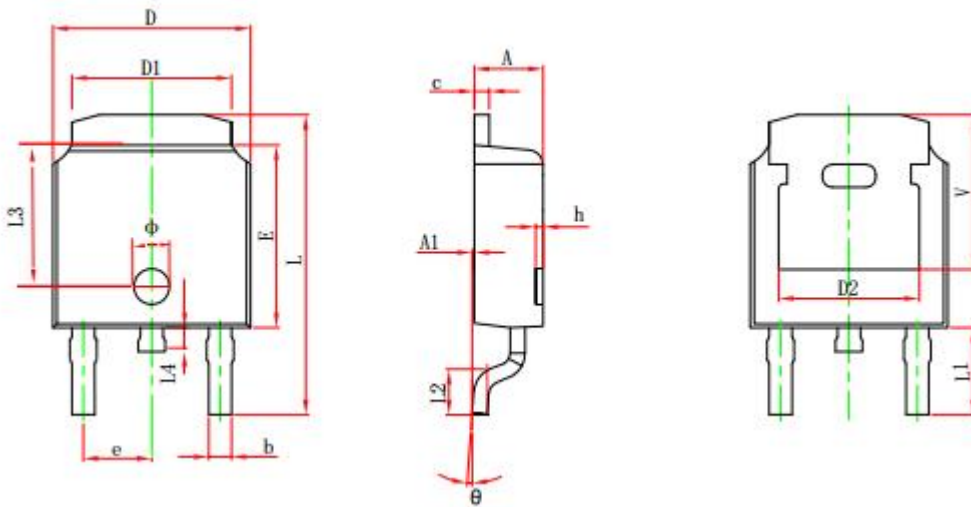


MOSFET ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Off characteristics						
Drain-Source breakdown Voltage	V(BR)DSS	VGS=0V, ID=250μA	600			V
Drain-Source diode forward Voltage	VSD	VGS=0V, IS=2.0A			1.5	V
Zero gate voltage drain current	IDSS	VDS=600V, VGS=0V			25	μA
Gate-body leakage current	IGSS	VDS=0V, VGS=±30V			±100	nA
On characteristics						
Gate-threshold voltage	VGS(th)	VDS=VGS, ID=250μA	2.0		4.0	V
Non-triggering gate voltage	RDS(on)	VGS=10V, ID=1.0A			5.0	Ω

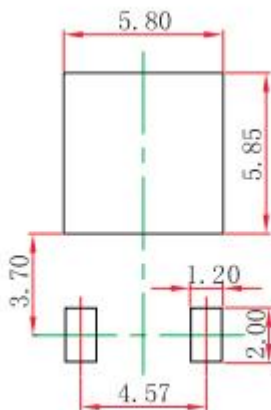


TO-252-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	4.460 REF.		0.1756 REF.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>ZG\(中鑫半导体\)](#)